

TECHNICAL DATA  
DATA SHEET 285, REV -

**TRANSIENT VOLTAGE SUPPRESSOR DIODE**  
(500 Watt)

DESCRIPTION: 5.2 VOLT, 175 MILLIAMP, AXIAL LEAD TRANSIENT VOLTAGE SUPPRESSOR DIODE.

MAX. RATINGS / ELECTRICAL CHARACTERISTICS All ratings are at  $T_A = 25^\circ\text{C}$  unless otherwise specified.

RATING	CONDITIONS	MIN	TYP	MAX	UNIT
Breakdown Voltage @ $I_{BR}$		6.12 6.46	-	-	Vdc
Test Current ( $I_{BR}$ )		-	-	175	mAmps dc
Working Peak Reverse Voltage ( $V_{RWM}$ )		-	-	5.2	Vdc
Maximum Reverse Current ( $I_{R1}$ )	$T_A = 25^\circ\text{C}$ $T_A = 125^\circ\text{C}$	-	-	100 500	$\mu\text{Amps dc}$
Maximum Clamp Voltage $V_{C(max)}$	@ $I_P, t_p = 1\text{ms}$	-	-	11.0 10.5	Volts (pk)
Maximum Peak Pulse Current ( $I_P$ )		-	-	45.4 47.6	Amps (pk)
Maximum Temperature Coefficient ( $V_{(BR)}$ )		-	-	.05	%/ $^\circ\text{C}$
Maximum Reverse Current ( $I_R$ )	@ $T_A = 150^\circ\text{C}$	-	-	4000	$\mu\text{Amps dc}$
Operating and Storage Temp. ( $T_{op}$ & $T_{stg}$ )		-55	-	+175	$^\circ\text{C}$

Notes:

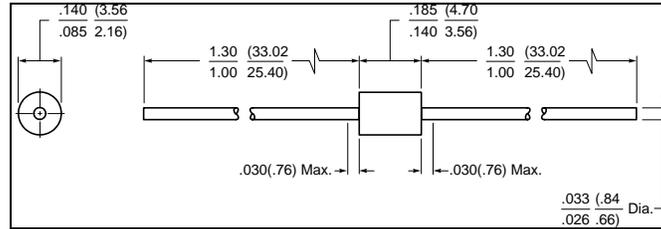
$P_R = 2\text{W}$  for 500W peak pulse power devices at  $T_A = +25^\circ\text{C}$ .

$P_R = 3\text{W}$  (for 500W peak pulse power devices at  $T_L = +75^\circ\text{C}$  for  $L = 0.375$  inch (9.53mm)).

$P_{PR} = 500\text{W}$

$-55^\circ\text{C} \leq T_{op} \leq +175^\circ\text{C}$ ,  $-55^\circ\text{C} \leq T_{stg} \leq +175^\circ\text{C}$  (ambient temperatures).

MECHANICAL DIMENSIONS In Inches / (mm), min./max.



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